



N-Channel 30-V (D-S), 175°C MOSFET

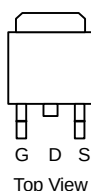
PRODUCT SUMMARY

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.013 @ $V_{GS} = 10$ V	45 ^a
	0.02 @ $V_{GS} = 4.5$ V	45 ^a

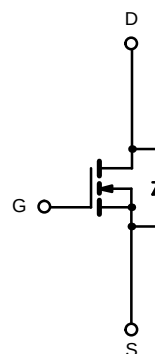
FEATURES

- TrenchFET® Power MOSFETS
- 175°C Junction Temperature

TO-263



SUB45N03-13L



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	$T_C = 25^\circ\text{C}$	I_D	45 ^a	A
	$T_C = 125^\circ\text{C}$		34 ^a	
Pulsed Drain Current		I_{DM}	100	
Avalanche Current		I_{AR}	45	
Repetitive Avalanche Energy ^b	$L = 0.1$ mH	E_{AR}	100	mJ
Maximum Power Dissipation ^b	$T_C = 25^\circ\text{C}$	P_D	88 ^c	W
	$T_A = 25^\circ\text{C}^d$		3.75	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Limit	Unit
Junction-to-Ambient	PCB Mount ^d	R_{thJA}	40	$^\circ\text{C/W}$
Junction-to-Case (Drain)		R_{thJC}	1.7	

Notes

- Package limited.
- Duty cycle $\leq 1\%$.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>

SUB45N03-13L

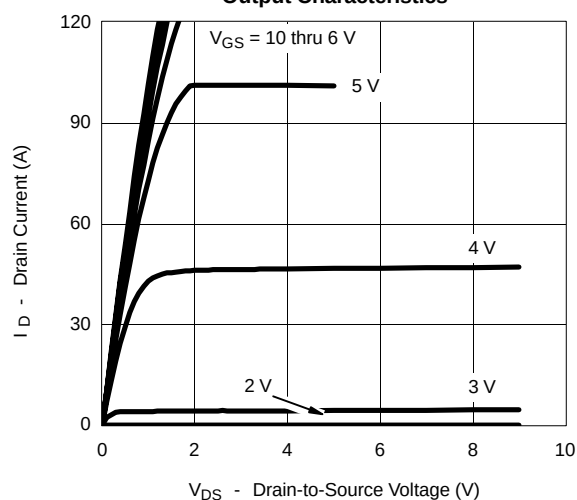
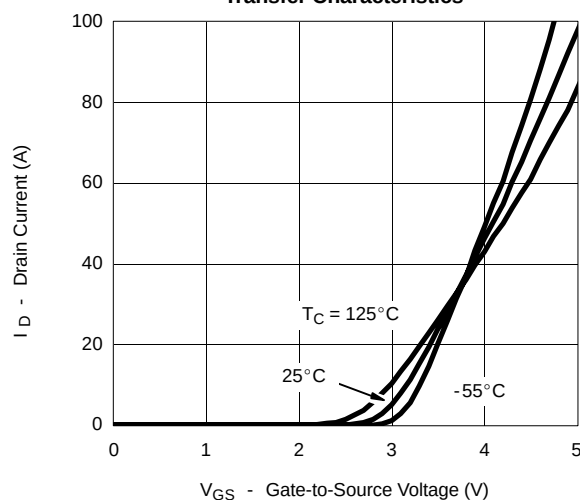
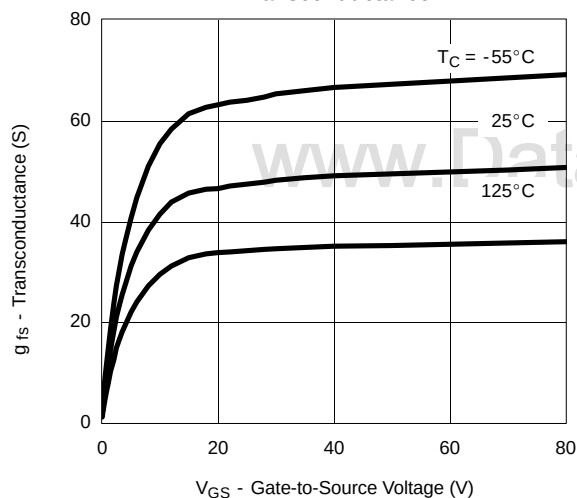
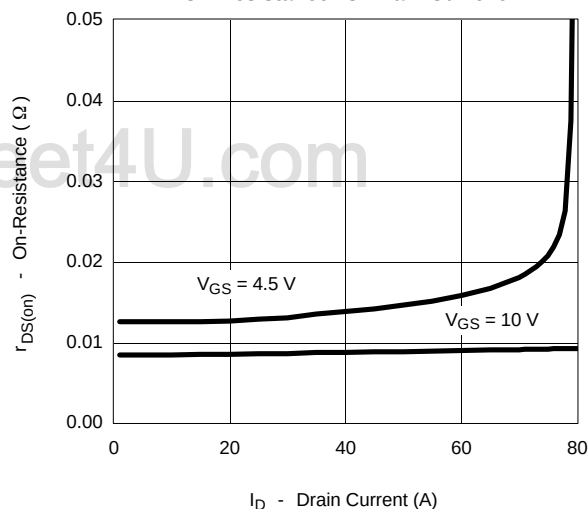
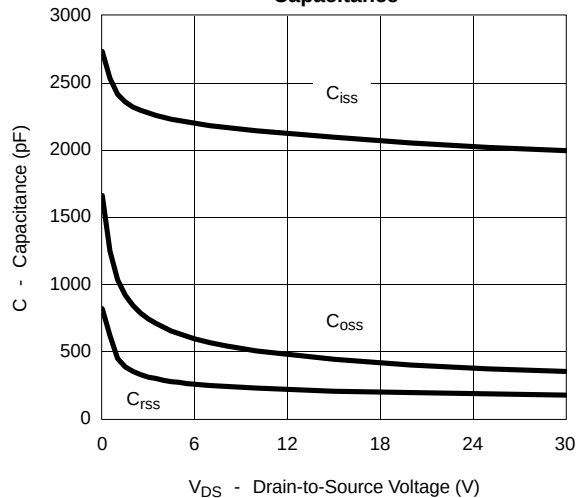
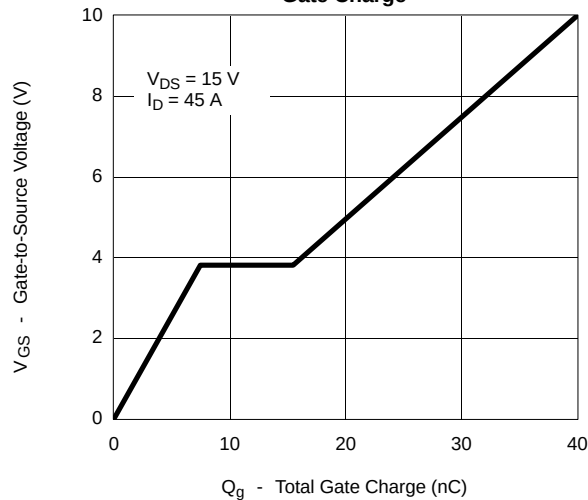


Vishay Siliconix

MOSFET SPECIFICATIONS (T _J =25° C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _{DS} = 250 μA	1		3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 125°C			50	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 175°C			150	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	45			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 45 A		0.009	0.013	Ω
		V _{GS} = 10 V, I _D = 45 A, T _J = 125°C		0.013	0.02	
		V _{GS} = 10 V, I _D = 45 A, T _J = 175°C		0.02	0.026	
		V _{GS} = 4.5 V, I _D = 20 A		0.0145	0.02	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 45 A	20			S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		2000		pF
Output Capacitance	C _{oss}			370		
Reversen Transfer Capacitance	C _{rss}			180		
Total Gate Charge ^c	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 45 A		40	70	nC
Gate-Source Charge ^c	Q _{gs}			7.5		
Gate-Drain Charge ^c	Q _{gd}			8		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 15 V, R _L = 0.33 Ω I _D ≈ 45 A, V _{GEN} = 10 V, R _G = 2.5 Ω		11	20	ns
Rise Time ^c	t _r			9	20	
Turn-Off Delay Time ^c	t _{d(off)}			38	70	
Fall Time ^c	t _f			11	20	
Source-Drain Diode Ratings and Characteristics (T _C = 25° C) ^b						
Continuous Current	I _s				45	A
Pulsed Current	I _{SM}				100	
Forward Voltage ^a	V _{SD}	I _F = 45 A, V _{GS} = 0 V		1	1.3	V
Reverse Recovery Time	t _{rr}	I _F = 45 A, di/dt = 100 A/μs		35	70	ns
Peak Reverse Recovery Current	I _{RM(REC)}			1.7		A
Reverse Recovery Charge	Q _{rr}			0.03		μC

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
e. Guaranteed by design, not subject to production testing.
b. Independent of operating temperature.

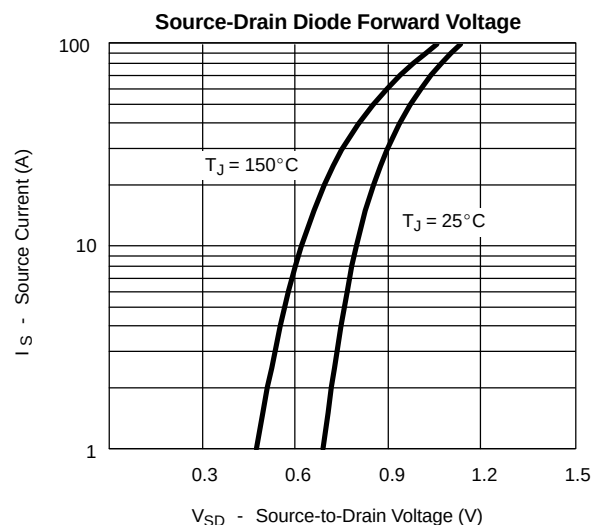
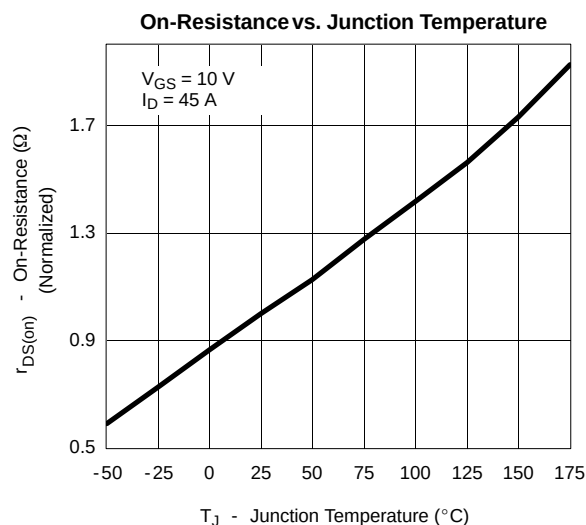

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)
Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge


SUB45N03-13L

Vishay Siliconix



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



THERMAL RATINGS

